

CWDM305P

**SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**



SOIC-8 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CWDM305P is a high current P-channel enhancement-mode silicon MOSFET, manufactured by the P-channel DMOS process, and is designed for high speed pulsed amplifier and driver applications. This MOSFET offers high current, low $r_{DS(ON)}$, low threshold voltage, and low leakage current.

MARKING CODE: C503P

APPLICATIONS:

- Load/Power switches
- Power supply converter circuits
- Battery powered portable equipment

FEATURES:

- Low $r_{DS(ON)}$ (83m Ω MAX @ $V_{GS}=5.0V$)
- High current ($I_D=5.3A$)

MAXIMUM RATINGS: ($T_A=25^\circ C$)

Drain-Source Voltage
Gate-Source Voltage
Continuous Drain Current (Steady State)
Maximum Pulsed Drain Current, $t_p=10\mu s$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{DS} 30
 V_{GS} 16
 I_D 5.3
 I_{DM} 21.2
 P_D 2.0
 T_J, T_{stg} -55 to +150
 θ_{JA} 62.5

UNITS

V
V
A
A
W
 $^\circ C$
 $^\circ C/W$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ C$ unless otherwise noted)

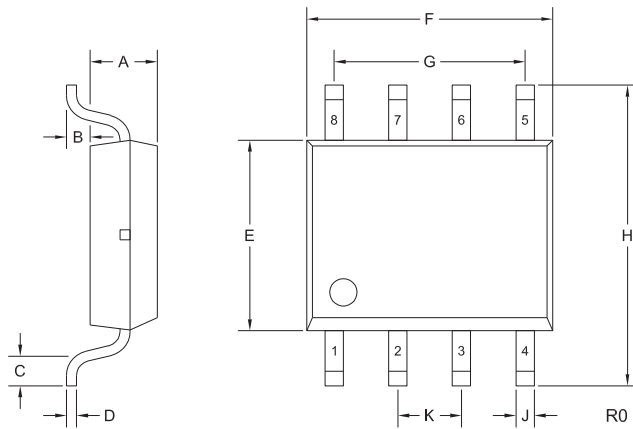
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=20V, V_{DS}=0$			100	nA
I_{DSS}	$V_{DS}=30V, V_{GS}=0$			1.0	μA
BV_{DSS}	$V_{GS}=0, I_D=250\mu A$	30			V
$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0		3.0	V
$r_{DS(ON)}$	$V_{GS}=10V, I_D=2.7A$		0.066	0.072	Ω
$r_{DS(ON)}$	$V_{GS}=5.0V, I_D=2.7A$		0.077	0.083	Ω
g_{FS}	$V_{DS}=5.0V, I_D=5.3A$		11		S
C_{rss}	$V_{DS}=10V, V_{GS}=0, f=1.0MHz$		50	60	pF
C_{iss}	$V_{DS}=10V, V_{GS}=0, f=1.0MHz$		500	590	pF
C_{oss}	$V_{DS}=10V, V_{GS}=0, f=1.0MHz$		60	150	pF
$Q_{g(tot)}$	$V_{DD}=15V, V_{GS}=5.0V, I_D=5.3A$		4.7	7.0	nC
Q_{gs}	$V_{DD}=15V, V_{GS}=5.0V, I_D=5.3A$		1.4	2.1	nC
Q_{gd}	$V_{DD}=15V, V_{GS}=5.0V, I_D=5.3A$		1.7	2.5	nC
t_{on}	$V_{DD}=15V, I_D=5.3A, R_G=10\Omega$		7.0		ns
t_{off}	$V_{DD}=15V, I_D=5.3A, R_G=10\Omega$		8.0		ns

R4 (23-August 2012)

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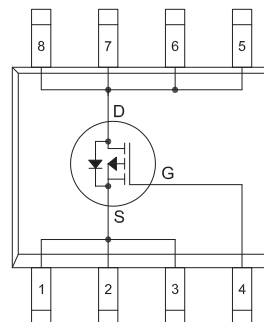
SOIC-8 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.049	0.057	1.24	1.44
B	0.000	0.011	0.00	0.27
C	0.018	-	0.46	-
D	0.006	0.011	0.16	0.27
E	0.145	0.154	3.70	3.90
F	0.189	0.198	4.81	5.01
G	0.150		3.81	
H	0.231	0.244	5.88	6.18
J	0.013	0.021	0.35	0.52
K	0.050		1.27	

SOIC-8 (REV: R0)

PIN CONFIGURATION



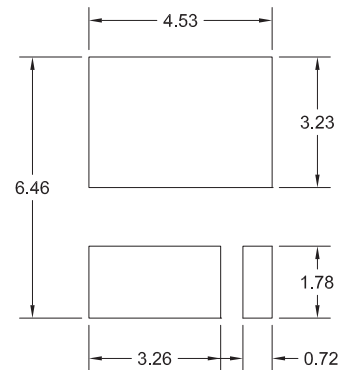
LEAD CODE:

- | | |
|-----------|----------|
| 1) Source | 5) Drain |
| 2) Source | 6) Drain |
| 3) Source | 7) Drain |
| 4) Gate | 8) Drain |

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SUGGESTED MOUNTING PADS

(Dimensions in mm)



R0

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